

In the Claims:

Please amend claims 7 and 18 to read as follows:

1. (Original) A method for producing porous Group III-V material, the method comprising steps of:

depositing a thin discontinuous layer of metal on a Group III-V material surface;

etching the Group III-V material surface in a HF and oxidant solution, said etching being conducted without external electrical bias.

2. (Original) The method according to claim 1, wherein said step of etching is conducted in the absence of illumination.

3. (Original) The method according to claim 1, wherein said step of etching is conducted in the presence of illumination.

4. (Original) The method according to claim 1, wherein said metal comprises Pt.

5. (Original) The method according to claim 1, wherein said metal comprises Au.

6. (Original) The method according to claim 1, wherein said metal comprises Pd.

7. (Currently amended) The method according to claim 1, wherein said metal comprises a combination of metals selected from the group consisting of Au, Pt and Pd.

8. (Original) The method according to claim 1, wherein said oxidant comprises H₂O₂.

9. (Original) The method according to claim 1, wherein the thickness of said metal is less than approximately 10nm.

10. (Original) The method according to claim 1, wherein said etching is conducted for a time period between about 2 seconds and one hour.

11. (Original) The method according to claim 1, wherein said Group III-V material comprises GaN.

12. (Original) A method for producing porous Group III-V material, the method consisting of the following steps:

depositing a thin discontinuous layer of metal on a Group III-V material surface;

etching the Group III-V material surface in a HF and oxidant solution for a period of about two seconds up to 60 minutes.

13. (Original) The method according to claim 12, wherein said step of etching is conducted in the absence of illumination.

14. (Original) The method according to claim 12, wherein said step of etching is conducted in the presence of illumination.

15. (Original)The method according to claim 12, wherein said metal comprises Pt.

16. (Original) The method according to claim 12, wherein said metal comprises Au.

17. (Original) The method according to claim 12, wherein said metal comprises Pd.

18. (Currently amended) The method according to claim 12, wherein said metal comprises a combination of metals selected from the group consisting of Au, Pt and Pd.

19. (Original) The method according to claim 12, wherein said oxidant comprises H₂O₂.

20. (Original) The method according to claim 12, wherein the thickness of said metal is less than approximately 10nm.

21. (Original) The method according to claim 12, wherein said etching is conducted for a time period between about 2 seconds and one hour.

22. (Original) The method according to claim 12, wherein said Group III-V material comprises GaN.

23. (Original) A method for producing porous Group III-V material, the method comprising steps of:

depositing metal on a Group III-V material surface in a thickness sufficient to permit nucleation that forms nanometer size metal particles and small enough to prevent formation of a continuous metal layer;

etching the Group III-V material surface in a HF and oxidant solution for a period of about two seconds up to 60 minutes, said etching being conducted without external electrical bias.